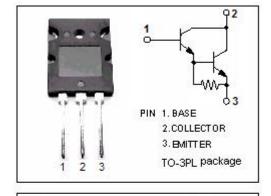




# **isc Silicon NPN Darlington Power Transistor**

#### **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 100V(Min)
- · High DC Current Gain-
  - : h<sub>FE</sub>= 5000( Min.) @(I<sub>C</sub>= 4A, V<sub>CE</sub>= 5V)
- · Low Collector Saturation Voltage-
  - :  $V_{CE(sat)}$ = 2.5V(Max)@ ( $I_C$ = 4A,  $I_B$ = 4mA)
- Complement to Type 2SB1502
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

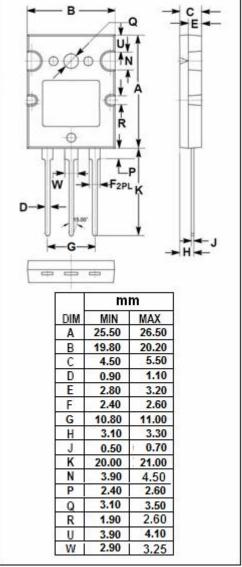


### **APPLICATIONS**

• Designed for power amplification.

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	V		
Vceo	Collector-Emitter Voltage	100	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
lc	Collector Current-Continuous	5	Α	
Ісм	Collector Current-Peak	8	Α	
P <sub>C</sub>	Collector Power Dissipation @T <sub>a</sub> =25°C	3.5	- W	
	Collector Power Dissipation @T <sub>C</sub> =25°C	60		
TJ	Junction Temperature	150	$^{\circ}\!\mathbb{C}$	
T <sub>stg</sub>	Storage Temperature	-55~150	$^{\circ}$ C	





## **isc Silicon NPN Darlington Power Transistor**

2SD2275

### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	100			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 4mA			2.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 4mA			3.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 120V; I <sub>E</sub> = 0			100	μА
Iceo	Collector Cutoff Current	V <sub>CE</sub> = 100V; I <sub>B</sub> = 0			100	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			100	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	2000			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4A; V <sub>CE</sub> = 5V	5000		30000	
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V		20		MHz

### h<sub>FE-2</sub> Classifications

Q	S	Р
5000-15000	7000-21000	8000-30000

### Notice:

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